



STD10NF06L

N-CHANNEL 60V - 0.1Ω - 10A DPAK

STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD10NF06L	60V	<0.12Ω	10A

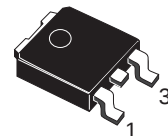
- TYPICAL R_{DS(on)} = 0.1Ω
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")

DESCRIPTION

This MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

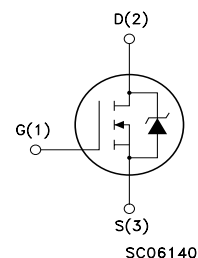
APPLICATIONS

- DC-DC & DC-AC CONVERTERS
- DC MOTOR CONTROL



DPAK

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	60	V
V _{GS}	Gate- source Voltage	± 15	V
I _D	Drain Current (continuous) at T _C = 25°C	10	A
I _D	Drain Current (continuous) at T _C = 100°C	7	A
I _{DM} (●)	Drain Current (pulsed)	40	A
P _{TOT}	Total Dissipation at T _C = 25°C	30	W
	Derating Factor	0.2	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	30	V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	50	mJ
T _{stg}	Storage Temperature	- 55 to 175	°C
T _j	Max. Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 10A, di/dt ≤ 400A/μs, V_{DD} = 48V, T_j ≤ T_{JMAX}.

(2) Starting T_j = 25°C, I_d = 7A, V_{DD} = 20 V

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THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	100	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	275	°C

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 15V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	1			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 5 A V _{GS} = 5 V, I _D = 5 A		0.1 0.12	0.12 0.14	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} = 15 V, I _D = 10A		6		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		346		pF
C _{oss}	Output Capacitance			54		pF
C _{rss}	Reverse Transfer Capacitance			22		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30V$, $I_D = 5A$		10		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 4.5V$ (see test circuit, Figure 3)		50		ns
Q_g	Total Gate Charge	$V_{DD} = 48V$, $I_D = 10A$, $V_{GS} = 5V$		6	8	nC
Q_{gs}	Gate-Source Charge			3		nC
Q_{gd}	Gate-Drain Charge			2.5		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 30V$, $I_D = 5A$, $R_G = 4.7\Omega$, $V_{GS} = 4.5V$		20		ns
t_f	Fall Time	(see test circuit, Figure 5)		10		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				10	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				40	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 10A$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 10A$, $di/dt = 100A/\mu s$, $V_{DD} = 20V$, $T_j = 150^\circ C$		30		ns
Q_{rr}	Reverse Recovery Charge	(see test circuit, Figure 5)		50		nC
I_{RRM}	Reverse Recovery Current			3		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

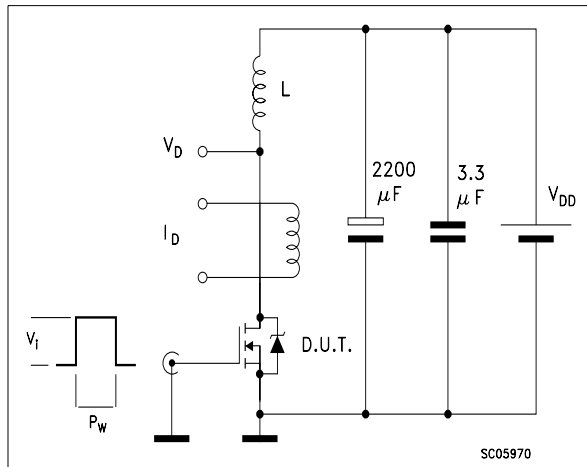


Fig. 2: Unclamped Inductive Waveform

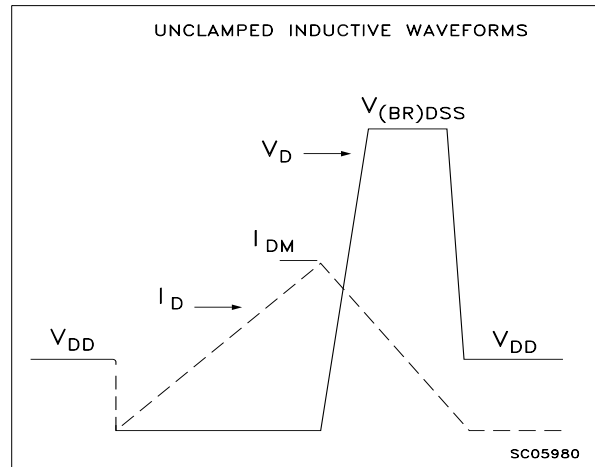


Fig. 3: Switching Times Test Circuit For Resistive Load

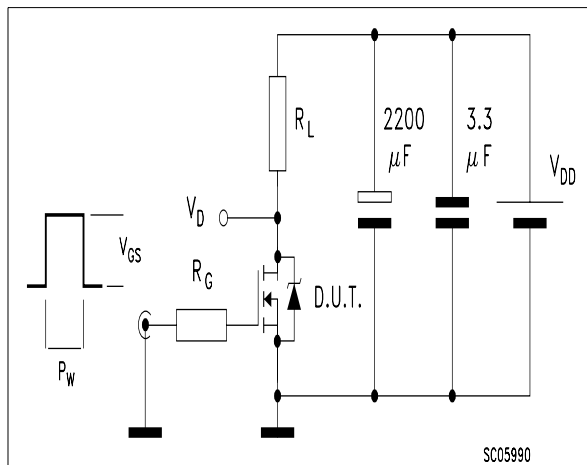


Fig. 4: Gate Charge test Circuit

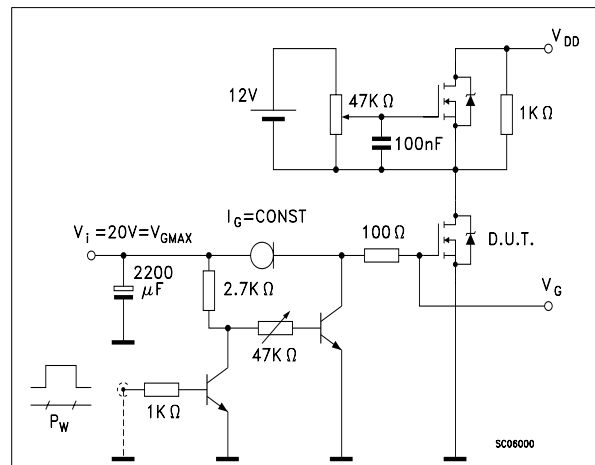
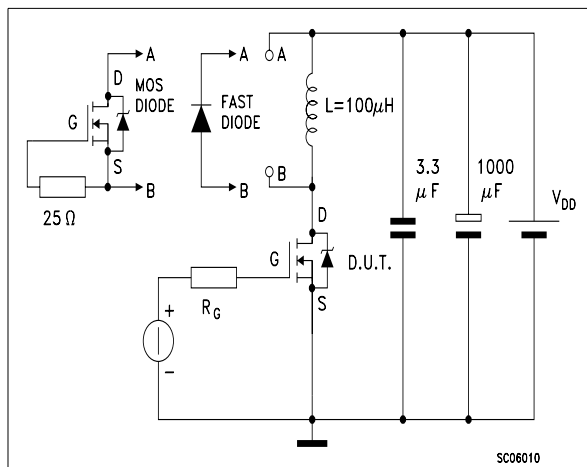
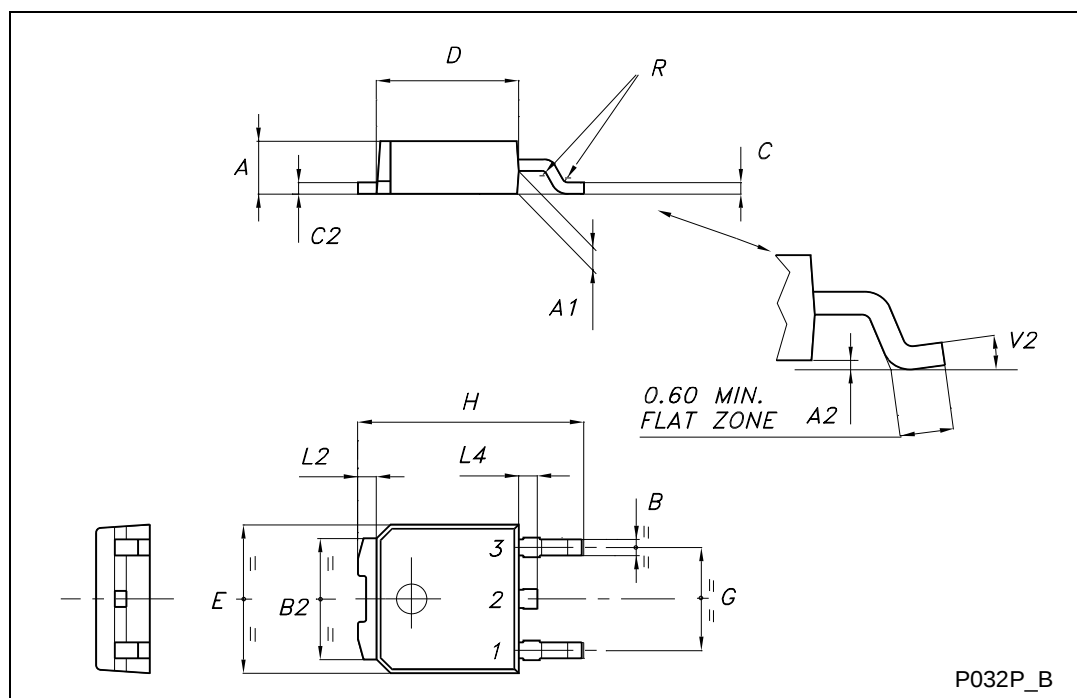


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

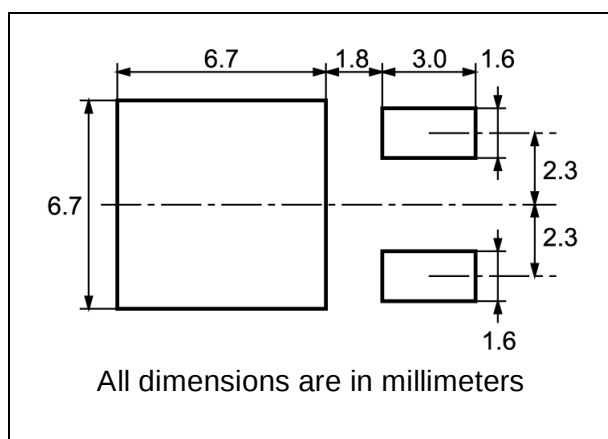


TO-252 (DPAK) MECHANICAL DATA

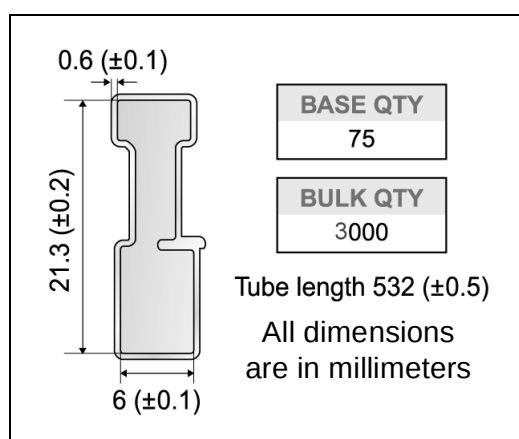
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



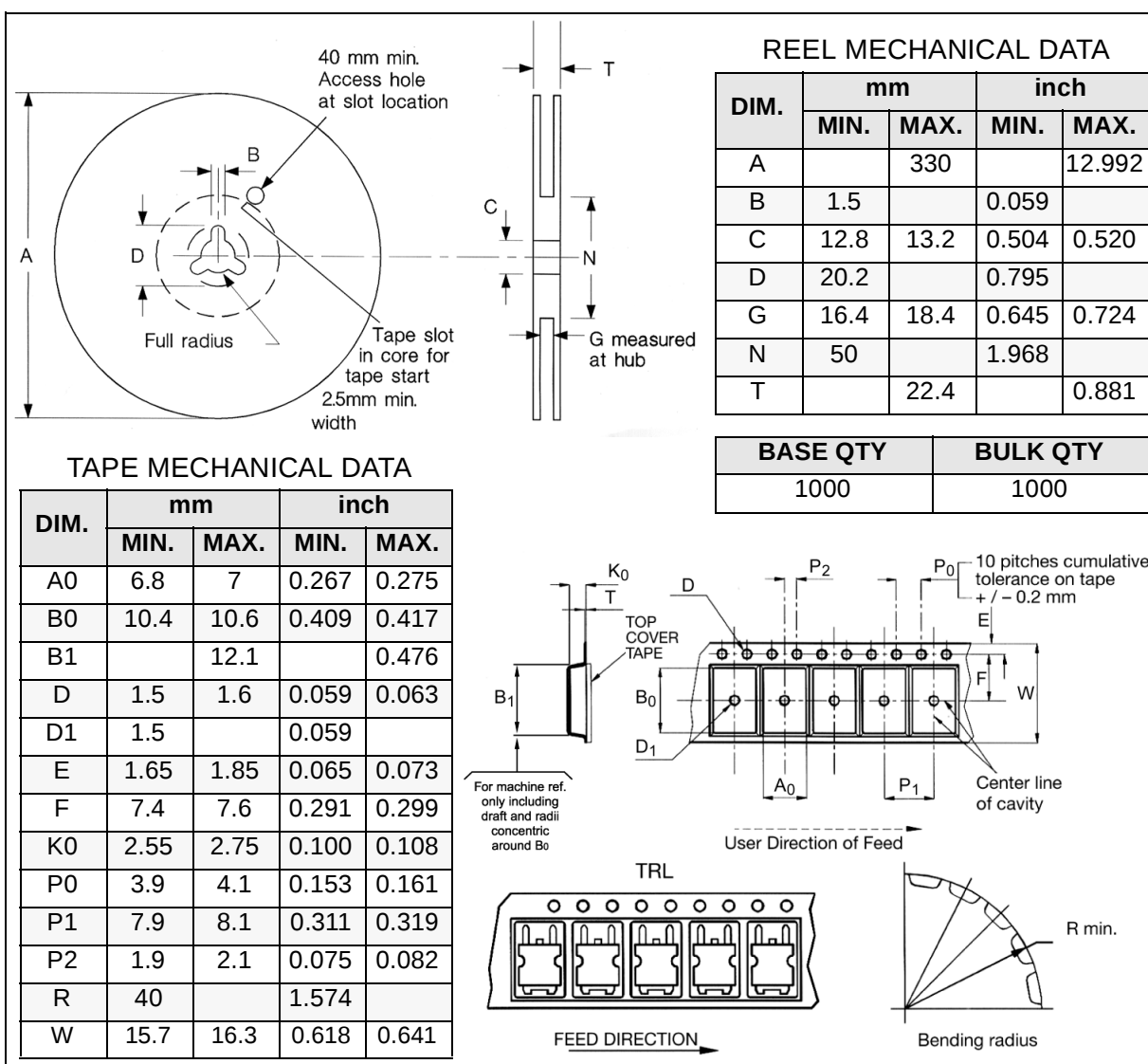
DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



* on sales type

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